

April 2007

QSC112, QSC113, QSC114 Plastic Silicon Infrared Phototransistor

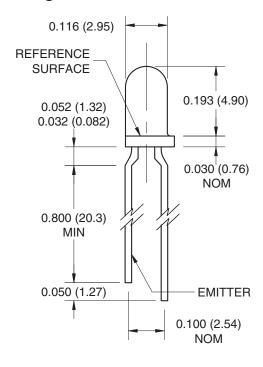
Features

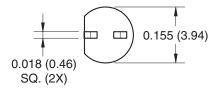
- Tight production distribution
- Steel lead frames for improved reliability in solder mounting
- Good optical-to-mechanical alignment
- Plastic package is infrared transparent black to attenuate visible light
- Can be used with QECXXX LED
- Black plastic body allows easy recognition from LED

Description

The QSC112/113/114 is a silicon phototransistor encapsulated in an infrared transparent, black T-1 package.

Package Dimensions



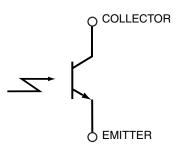


Notes:

- 1. Dimensions of all drawings are in inches (mm).
- 2. Tolerance is ± 0.10 (.25) on all non-nominal dimensions unless otherwise specified.



Schematic



Absolute Maximum Ratings (T_A = 25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
T _{OPR}	Operating Temperature	-40 to +100 °C	
T _{STG}	Storage Temperature	-40 to +100	°C
T _{SOL-I}	Soldering Temperature (Iron) ^(2,3,4)	240 for 5 sec	°C
T _{SOL-F}	Soldering Temperature (Flow) ^(2,3)	260 for 10 sec	°C
V _{CE}	Collector-Emitter Voltage	30	V
V _{EC}	Emitter-Collector Voltage	5	V
P _D	Power Dissipation ⁽¹⁾	100	mW

Notes:

- 1. Derate power dissipation linearly 1.33 mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron 1/16" (1.6mm) minimum from housing.

Electrical/Optical Characteristics (T_A =25°C)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
λ _{PS}	Peak Sensitivity Wavelength			880		nm
Θ	Reception Angle			±4		0
I _{CEO}	Collector-Emitter Dark Current	V _{CE} = 10 V, Ee = 0			100	nA
BV _{CEO}	Collector-Emitter Breakdown	I _C = 1 mA	30			V
BV _{ECO}	Emitter-Collector Breakdown	I _E = 100 μA	5			V
I _{C(ON)}	On-State Collector Current QSC112	Ee = 0.5 mW/cm ² , $V_{CE} = 5 V^{(5)}$	1		4	mA
	On-State Collector Current QSC113		2.40		9.60	
	On-State Collector Current QSC114		4.00			
V _{CE(sat)}	Saturation Voltage	Ee = 0.5 mW/cm^2 , $I_C = 0.5 \text{ mA}^{(5)}$			0.4	V
t _r	Rise Time	$V_{CC} = 5 \text{ V}, R_L = 100 \Omega, I_C = 2 \text{ mA}$		5.0		μs
t _f	Fall Time			5.0		

Note:

5. λ = 880 nm, AlGaAs.

Typical Performance Curves

I_{C(ON)} - Light Current (mA)

10¹

10⁻¹∟ 0.1

Figure 1. Light Current vs. Radiant Intensity

VCE = 5V
GaAs Light Source

Figure 2. Angular Response Curve

120° 90° 80° 70° 60°
130° 140°
150° 150°
160°
170°
180° 1.0 0.8 0.6 0.4 0.2 0.0 0.2 0.4 0.6 0.8 1.0

Figure 3. Dark Current vs. Collector - Emitter Voltage

E_e - Radiant Intensity (mW/cm²)

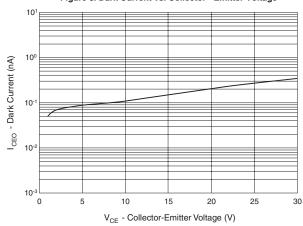


Figure 4. Light Current vs. Collector - Emitter Voltage

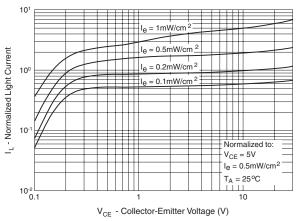
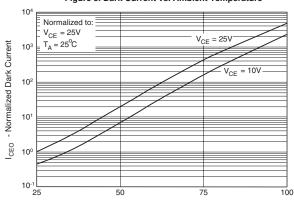


Figure 5. Dark Current vs. Ambient Temperature







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Rev. I26